



New Product

**SUR50N03-16P**  
Vishay Siliconix

## N-Channel 30-V (D-S) MOSFET

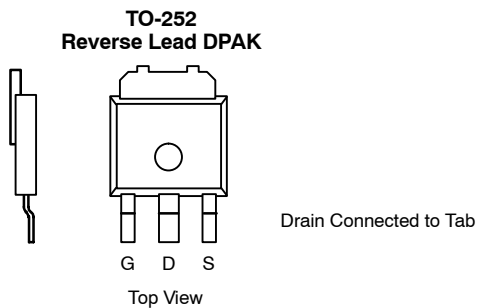
PRODUCT SUMMARY		
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>
30	0.016 @ V <sub>GS</sub> = 10 V	15
	0.024 @ V <sub>GS</sub> = 4.5 V	12

### FEATURES

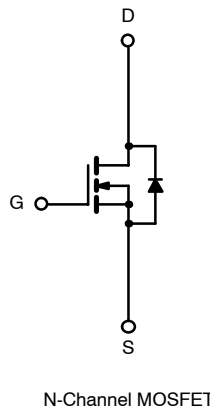
- TrenchFET® Power MOSFET
- PWM Optimized
- 100% R<sub>g</sub> Tested

### APPLICATIONS

- DC/DC Converters
  - High-Side
- Synchronous Rectifiers



Ordering Information:  
SUR50N03-16P—E3  
SUR50N03-16P-T4—E3 (alternate tape orientation)



ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V <sub>DS</sub>	30	V
Gate-Source Voltage		V <sub>GS</sub>	±20	
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 25°C	I <sub>D</sub>	36	A
	T <sub>A</sub> = 25°C		15	
	T <sub>A</sub> = 100°C		10.6	
Pulsed Drain Current		I <sub>DM</sub>	40	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	5	
Single Pulse Avalanche Current		I <sub>AS</sub>	25	mJ
Single Pulse Avalanche Energy		E <sub>AS</sub>	31.25	
Maximum Power Dissipation	T <sub>C</sub> = 25°C	P <sub>D</sub>	40.8	W
	T <sub>A</sub> = 25°C		6.5 <sup>a</sup>	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 10 sec	R <sub>thJA</sub>	18	23	°C/W
	Steady State		40	50	
Maximum Junction-to-Case		R <sub>thJC</sub>	3.0	3.7	

Notes  
a. Surface Mounted on FR4 Board, t ≤ 10 sec.

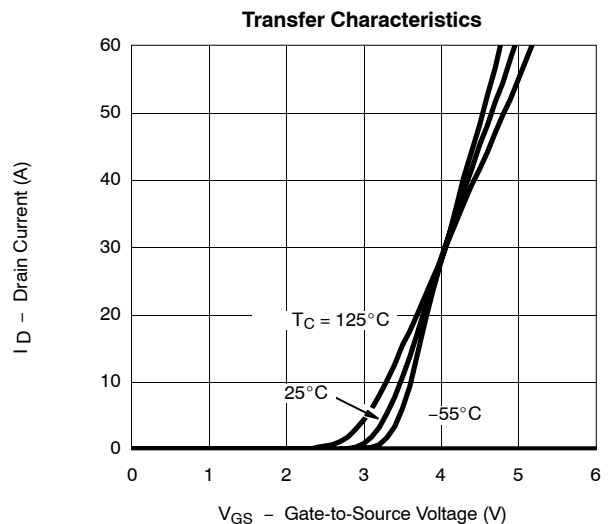
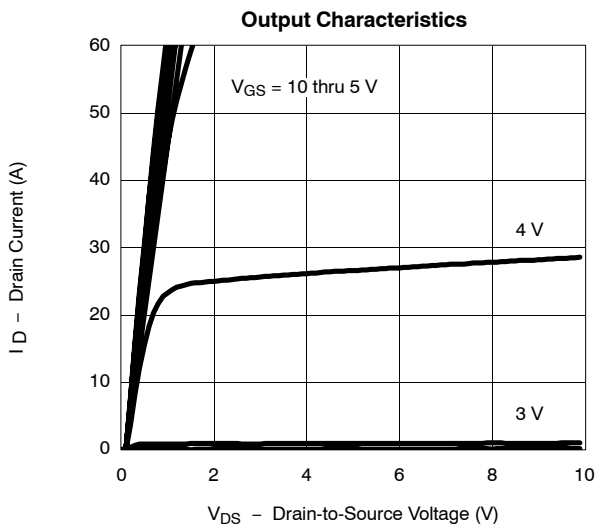


<b>SPECIFICATIONS (T<sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)</b>						
Parameter	Symbol	Test Condition	Min	Typ <sup>a</sup>	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	30			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.0		3.0	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	40			A
Drain-Source On-State Resistance <sup>b</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A		0.0128	0.016	Ω
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C			0.025	
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A		0.019	0.024	
Forward Transconductance <sup>b</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A	10			S
<b>Dynamic<sup>a</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz		1150		pF
Output Capacitance	C <sub>oss</sub>			215		
Reverse Transfer Capacitance	C <sub>rss</sub>			70		
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 50 A		8.5	13	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			5		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			2.5		
Gate Resistance	R <sub>g</sub>		2.7	5.5	9.40	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 15 V, R <sub>L</sub> = 0.3 Ω I <sub>D</sub> ≅ 50 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 2.5 Ω		7	15	ns
Rise Time <sup>c</sup>	t <sub>r</sub>			20	30	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			25	40	
Fall Time <sup>c</sup>	t <sub>f</sub>			12	20	
<b>Source-Drain Diode Ratings and Characteristic (T<sub>C</sub> = 25 °C)</b>						
Pulsed Current	I <sub>SM</sub>				40	A
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V		1.0	1.5	V
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 40 A, di/dt = 100 A/μs		25	70	ns

**Notes**

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- c. Independent of operating temperature.

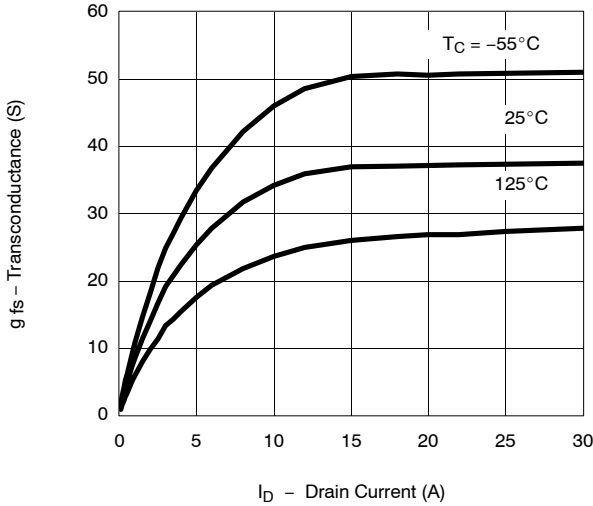
**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**



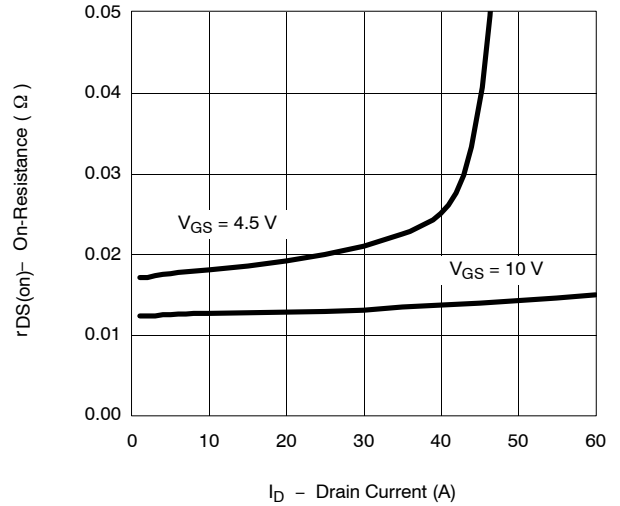


**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**

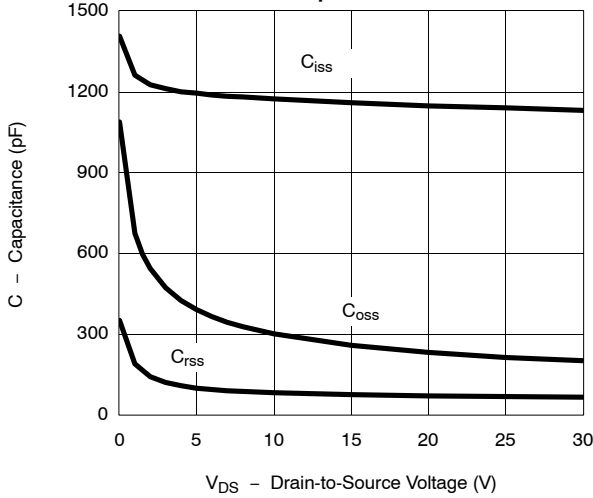
Transconductance



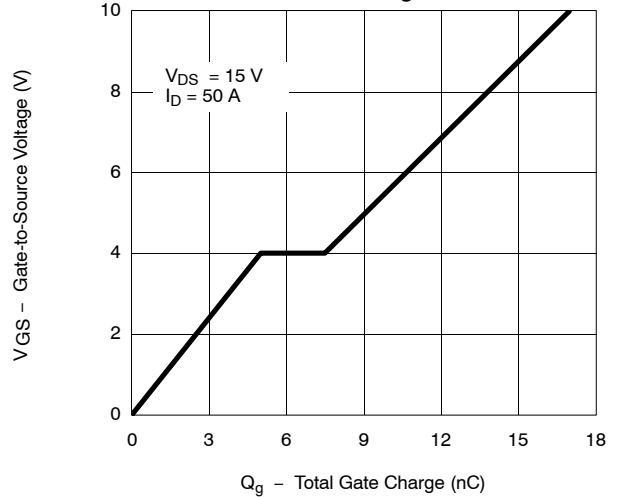
On-Resistance vs. Drain Current



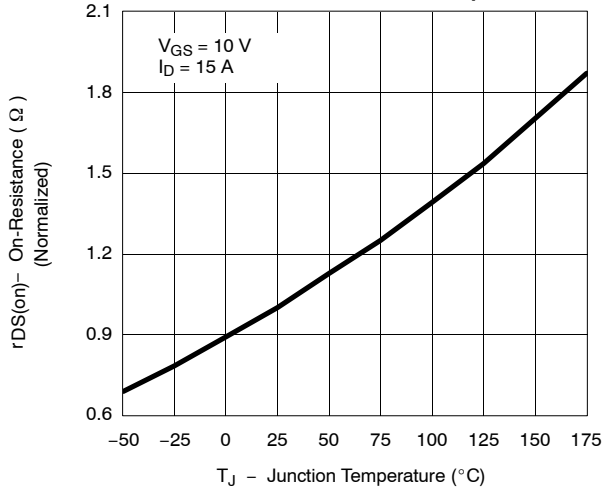
Capacitance



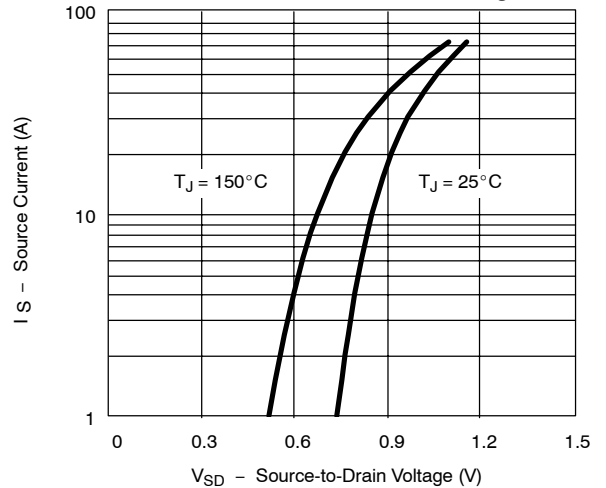
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage





**THERMAL RATINGS**

